

PN4143



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PNP General Purpose Amplifier

This device is designed for use as general purpose amplifiers and switches requiring collector currents to 500 mA. Sourced from Process 63. See PN2907A for characteristics.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units	
V_{CEO}	Collector-Emitter Voltage	40	V	
V _{CBO}	Collector-Base Voltage	60	V	
V_{EBO}	Emitter-Base Voltage	5.0	V	
I _C	Collector Current - Continuous	800	mA	
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C	

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

Thermal Characteristics TA = 25°C unless otherwise noted				
Symbol	Characteristic	Мах	Units	
		PN4143		
P _D	Total Device Dissipation Derate above 25°C	625 5.0	mW mW/°C	
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W	

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PNP General Purpose Amplifier

(continued)

OFF CHARACTERISTICS

V _{(BR)CEO}	Collector-Emitter Breakdown Voltage*	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 0$	40		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_{C} = 10 \mu A, I_{E} = 0$	60		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_{E} = 10 \ \mu A, I_{C} = 0$	5.0		V
ICEX	Collector Cutoff Current	$V_{CE} = 30 \text{ V}, V_{OB} = 0.5 \text{ V}$		50	nA
I _{BL}	Base Cutoff Current	$V_{CE} = 30 \text{ V}, V_{OB} = 0.5 \text{ V}$		50	nA

ON CHARACTERISTICS*

h _{FE}	DC Current Gain	$V_{CE} = 10 \text{ V}, I_C = 100 \mu\text{A}$ $V_{CE} = 10 \text{ V}, I_C = 1.0 m\text{A}$	35 50		
		$V_{CE} = 10 \text{ V}, I_{C} = 10 \text{ mA}$ $V_{CE} = 10 \text{ V}, I_{C} = 150 \text{ mA}$	75 100	300	
		$V_{CE} = 10 \text{ V}, I_{C} = 500 \text{ mA}$ $V_{CE} = 1.0 \text{ V}, I_{C} = 150 \text{ mA}$	30 50		
$V_{\text{CE}(\text{sat})}$	Collector-Emitter Saturation Voltage	$I_{\rm C} = 150 \text{ mA}, I_{\rm B} = 15 \text{ mA}$ $I_{\rm C} = 500 \text{ mA}, I_{\rm B} = 50 \text{ mA}$		0.4 1.6	V V
$V_{\text{BE}(\text{sat})}$	Base-Emitter Saturation Voltage	$I_{\rm C} = 150 \text{ mA}, I_{\rm B} = 15 \text{ mA}$ $I_{\rm C} = 500 \text{ mA}, I_{\rm B} = 50 \text{ mA}$		1.3 2.6	V V

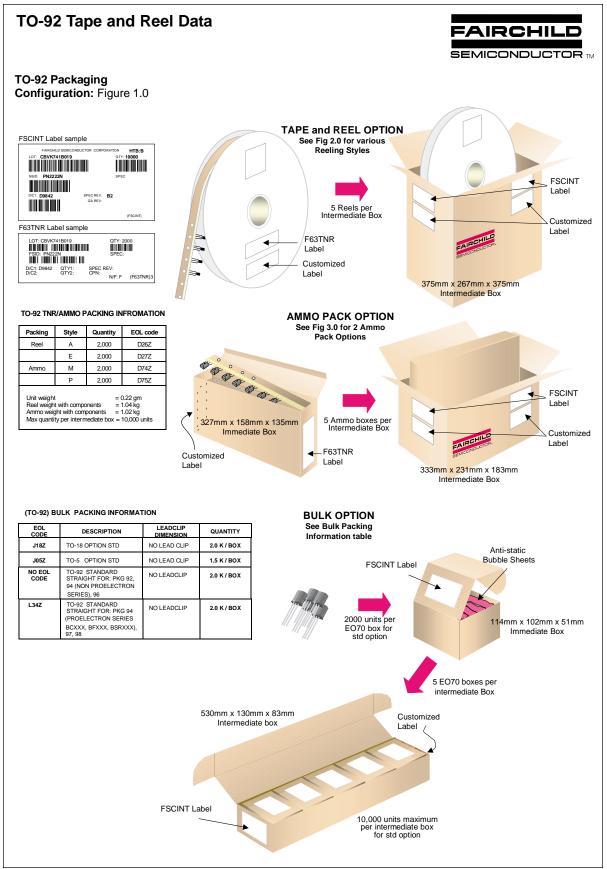
SMALL SIGNAL CHARACTERISTICS

C _{ob}	Output Capacitance	$V_{CB} = 10 \text{ V}, \text{ f} = 100 \text{ kHz}$		8.0	pF
C _{ib}	Input Capacitance	$V_{EB} = 2.0 \text{ V}, \text{ f} = 100 \text{ kHz}$		30	pF
h _{fe}	Small-Signal Current Gain	$I_{C} = 50 \text{ mA}, V_{CE} = 20 \text{ V},$ f = 100 MHz	2.0		

SWITCHING CHARACTERISTICS

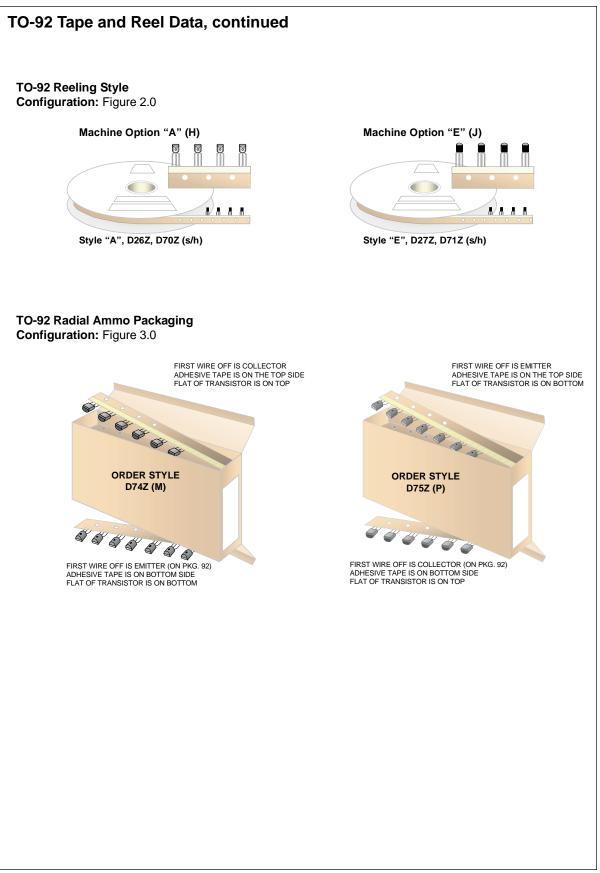
t _{on}	Turn-on Time	$V_{\rm CC} = 30 \text{ V}, \text{ I}_{\rm C} = 150 \text{ mA},$	45	ns
t _d	Delay Time	I _{B1} = 15 mA	10	ns
tr	Rise Time	1	40	ns
t _{off}	Turn-off Time	$V_{CC} = 30 \text{ V}, I_{C} = 150 \text{ mA}$	100	ns
ts	Storage Time	I _{B1} = I _{B2} = 15 mA	80	ns
t _f	Fall Time	1	30	ns

*Pulse Test: Pulse Width \leq 300 µs, Duty Cycle \leq 2.0%



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